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TYSiC

Guangdong Tianyu Semiconductor Co., Ltd.

廣東天域半導體股份有限公司

(A joint stock company incorporated in the People's Republic of China with limited liability)

(Stock Code: 2658)

**VOLUNTARY ANNOUNCEMENT
IN RELATION TO THE ENTERING INTO OF
A STRATEGIC COOPERATION AGREEMENT**

This announcement is made by Guangdong Tianyu Semiconductor Co., Ltd. (the “**Company**”, together with its subsidiaries, the “**Group**”) on a voluntary basis to provide the shareholders of the Company (the “**Shareholders**”) and potential investors of the Company with an update on the latest business development of the Group.

The board (the “**Board**”) of directors (the “**Director(s)**”) of the Company is pleased to announce that, on January 16, 2026 (after trading hours), the Company and Qinghe Jingyuan Semiconductor Technology (Group) Co., Ltd.* (青禾晶元半導體科技(集團)有限公司) (“**Qinghe Jingyuan**”) entered into a strategic cooperation agreement (the “**Agreement**”), pursuant to which the parties to the Agreement (each a “**Party**”, and collectively, the “**Parties**”) agreed to establish a strategic cooperation to jointly carry out the process development and technological iteration of bonding materials (including bonded silicon carbide (SiC), silicon on insulator (SOI), piezoelectric on insulator (POI), and ultra-large size (12 inches and above) SiC composite heat dissipation baseplates), leveraging the Company’s advantages in silicon carbide materials and Qinghe Jingyuan’s capabilities in the customization and optimization of bonding equipment.

THE AGREEMENT

The principal terms of the Agreement are outlined as follows:

Parties

- (i) The Company; and
- (ii) Qinghe Jingyuan.

Contents of Cooperation

1. **Process Development:** The Company shall carry out process development and mass production introduction of bonded materials, including bonded SiC, SOI, POI, 12-inch SiC composite heat dissipation baseplates, and interposers.
2. **Equipment and Technical Support:** Qinghe Jingyuan shall provide the Company with equipment and relevant technical support regarding ion implantation, wafer-level bonding, precision polishing, crystal repair, and stripping. This primarily involves:
 - Providing equipment customization, optimization, and process tuning for single crystal-polycrystalline SiC bonding substrates (8-inch);
 - Providing whole-line equipment selection, equipment customization, process optimization, and mass production support for single crystal-single crystal SiC bonding substrates (8-inch), SOI (8-inch and 12-inch), and Si on SiC (12-inch) bonding substrates; and
 - Providing bonding equipment suitable for materials such as diamond, gallium oxide (Ga_2O_3), gallium nitride (GaN), lithium niobate, and lithium tantalate.
3. **Equipment Improvement and Technical Support:** The Company shall provide guidance on equipment improvement and upgrades from the perspectives of process development and mass production. Qinghe Jingyuan shall cooperate with the Company's mass production requirements, increase research and development investment, and enhance equipment capabilities. Qinghe Jingyuan shall also actively cooperate to address technical issues encountered by the Company during use.
4. **Intellectual Property:** During the technical development process, intellectual property rights independently developed by each Party shall remain owned by such Party independently.

5. **Priority Cooperation:** During the term of the cooperation, under equivalent conditions, the Company shall give priority to cooperating with Qinghe Jingyuan for whole-line projects and give priority to purchasing related equipment from Qinghe Jingyuan. However, in the event that the equipment provided by Qinghe Jingyuan fails to meet the Company's technical specifications, mass production yield requirements, or delivery schedules, the Company shall have the right to procure from third parties, which shall not be deemed as a breach of contract.

Term

The cooperation term shall commence from January 16, 2026 to January 15, 2029.

INFORMATION REGARDING QINGHE JINGYUAN

Qinghe Jingyuan is a company established in the People's Republic of China focusing on semiconductor bonding integration technology. Its core business covers the research, development and manufacturing of high-end bonding equipment and precision bonding process foundry services. Its technology is applied in frontier fields such as advanced packaging, semiconductor device manufacturing, wafer-level heterogeneous material integration, and MEMS sensors.

Based on publicly available information, Qinghe Jingyuan is directly owned as to 22.25% by Mu Fengwen (母鳳文), with the remainder 77.75% of equity interest in Qinghe Jingyuan owned by 43 shareholders each holding less than 10%.

To the best of the Directors' knowledge, information, and belief, having made all reasonable enquiries, Qinghe Jingyuan and its ultimate beneficial owners are independent third parties not connected with the Company and its connected persons (as defined in the Rules Governing the Listing of Securities on The Stock Exchange of Hong Kong Limited).

REASONS FOR AND BENEFITS OF ENTERING INTO THE AGREEMENT

The Company primarily engaged in the production and sales of SiC epitaxial wafers. Its product portfolio includes 4-inch, 6-inch and 8-inch SiC epitaxial wafers. The Company's products are mainly used in industries including electric vehicles, photovoltaics, and rail transportation. The Company also provides value-added SiC epitaxial wafer related services, including SiC epitaxial foundry service, epitaxial wafer cleaning service, and substrate and epitaxial wafer inspection service.

The Board believes that the Parties will leverage their respective competitive advantages to establish a mutually beneficial partnership. By combining the Company's industrial strengths in the SiC epitaxial wafer sector with Qinghe Jingyuan's expertise in bonding integration technology and equipment, the cooperation aims to facilitate the development of advanced bonding material solutions and optimize production processes. This collaboration is expected to enhance the Group's technical capabilities in large-size composite baseplates, ensure equipment stability, and further consolidate the Group's market position.

The Board considers that the cooperation with Qinghe Jingyuan will be beneficial to the Group's future development and is in the interests of the Company and its Shareholders as a whole.

By order of the Board
Guangdong Tianyu Semiconductor Co., Ltd.
Li Xiguang
Chairman and executive director

Hong Kong, January 16, 2026

As of the date of this announcement, the Board comprises Mr. LI Xiguang as executive Director, Mr. AU YEUNG Chung and Mr. JIANG Dacai as non-executive Directors, Mr. HE Zhengsheng, Ms. LI Min and Mr. CHIN Vincent as independent non-executive Directors.

** for identification purpose only*